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In the Claims:

C1

1 1. (twice amended) A method of preparing a carbon-doped group  
2 III-V compound semiconductor crystal, comprising the steps of:  
3 placing a compound raw material, solid carbon, and a boron  
4 oxide substance into a crucible or a boat,  
5 sealing said crucible or boat containing said compound raw  
6 material, said solid carbon, and said boron oxide substance  
7 within an airtight vessel formed of a gas impermeable material,  
8 heating and melting said compound raw material in said  
9 crucible or said boat sealed within said airtight vessel, and  
10 solidifying said melted compound raw material to grow a  
11 carbon-doped compound semiconductor crystal. [.]  
12 wherein an amount of said solid carbon placed into said  
13 crucible or said boat is larger than an amount of carbon doped  
14 into said compound semiconductor crystal.

Claims 2 to 5 remain as previously amended.

Please cancel claim 6.

Claim 7,

line 2, after "claim", replace "6", by --1--.

Claims 8 to 20 remain as previously amended.

Claim 21 is maintained unchanged.

3442/WFF:nr

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